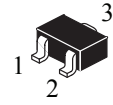


PNP TRANSISTOR
 **Lead(Pb)-Free**
FEATURES:

- * High voltage and high current
- * Excellent hFE linearity
- * Complementary to 2SC4738


SOT-523(SC-75)
MAXIMUM RATINGS (T_A=25°C unless otherwise noted)

Parameter	Symbol	Value	Units
Collector-Base Voltage	V _{CBO}	-50	V
Collector-Emitter Voltage	V _{CEO}	-50	V
Emitter-Base Voltage	V _{EBO}	-5	V
Collector Current Continuous	I _C	-150	mA
Total Device Dissipation	P _D	100	mW
Thermal Resistance Junction to Ambient	R _{θJA}	125	°C/W
Junction Temperature	T _J	-55 to +125	°C
Storage Temperature	T _{stg}	-55 to +125	°C

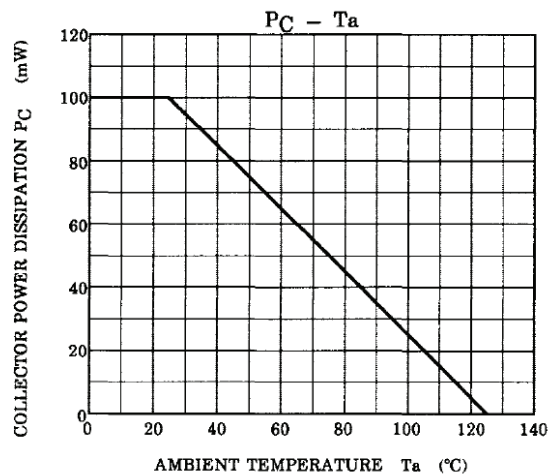
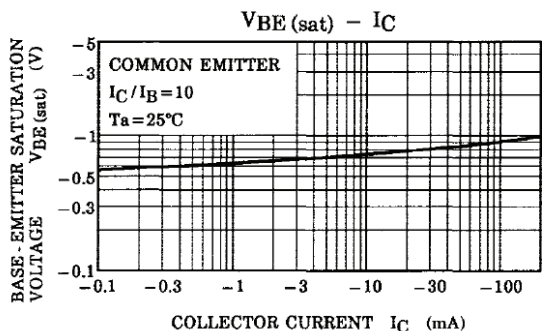
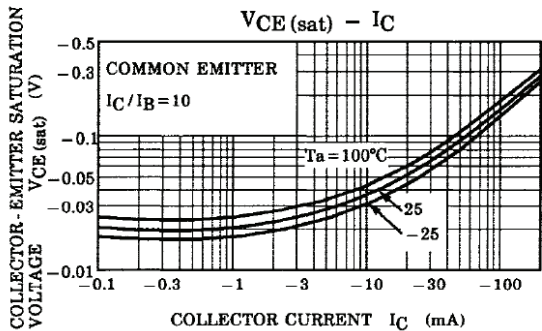
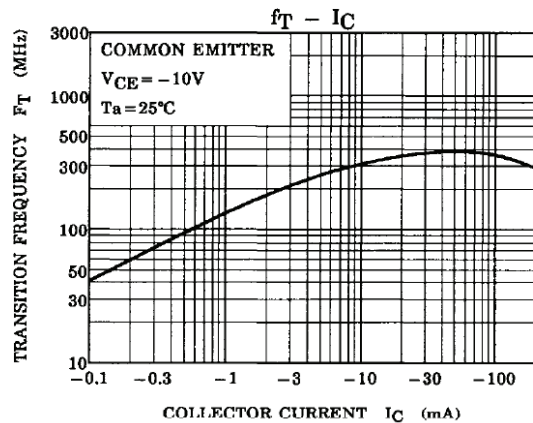
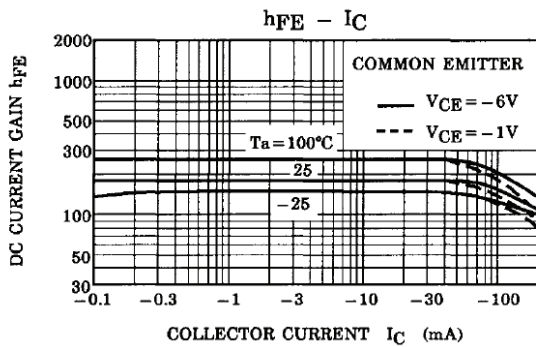
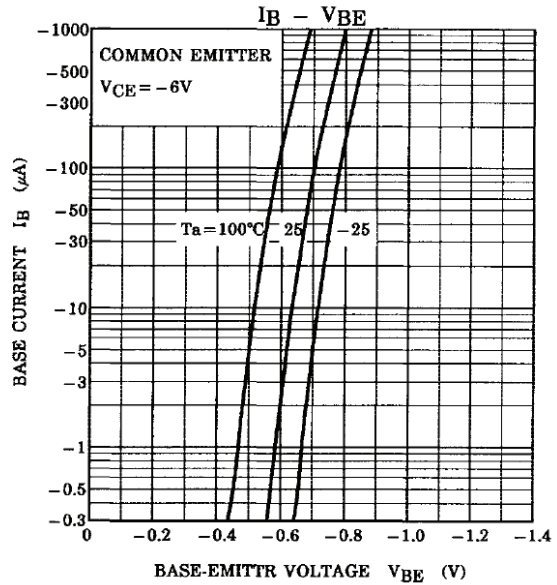
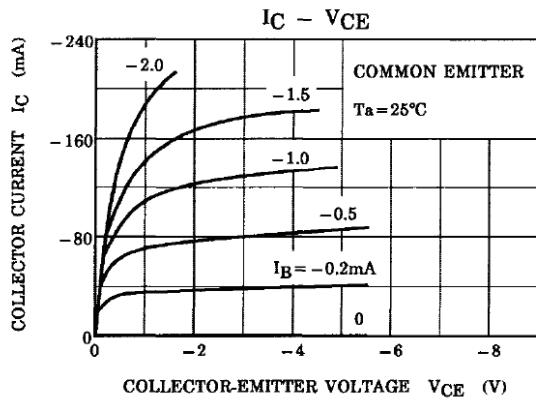
ELECTRICAL CHARACTERISTICS (T_{amb}=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V _{CBO}	I _C =-100μA, I _E =0	-50			V
Collector-emitter breakdown voltage	V _{CEO*}	I _C =-1mA, I _B =0	-50			V
Emitter-base breakdown voltage	V _{EBO}	I _E =-100μA, I _C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} =-50V, I _E =0			-100	nA
Emitter cut-off current	I _{EBO}	V _{EB} =-5V, I _C =0			-100	nA
DC current gain	h _{FE}	V _{CE} =-6V, I _C =-2mA	120		400	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-100mA, I _B =-10mA			-0.3	V
Transition frequency	f _T	V _{CE} =-10V, I _C =-1mA	80			MHz
Collector output capacitance	C _{ob}	V _{CB} =-10V, I _E =0, f=1MHz		4	7	pF

CLASSIFICATION OF h_{FE}

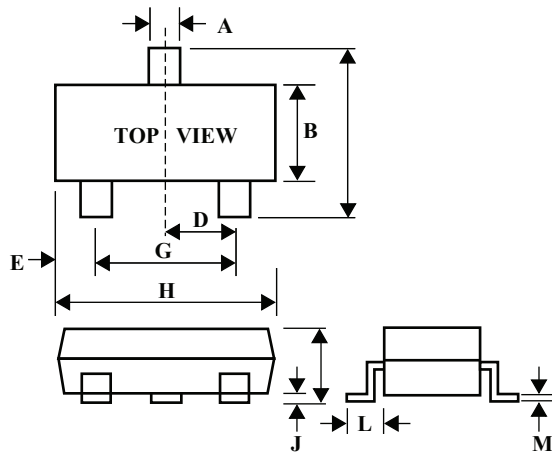
Rank	Y	GR
Range	120-240	200-400
Marking	SY	SG

Typical Characteristics



SOT-523 Outline Dimensions (SC-75)

Unit:mm



SOT-523		
Dim	Min	Max
A	0.30	0.50
B	0.70	0.90
C	1.45	1.75
D	-	0.50
E	0.15	0.40
G	0.80	1.00
H	1.40	1.80
J	0.00	0.10
K	0.70	1.00
L	0.37	0.48
M	0.10	0.25